1. General description

PNP low V_{CEsat} transistor and NPN Resistor-Equipped Transistor (RET) in a SOT457 (SC-74) small Surface Mounted Device (SMD) plastic package.

2. Features and benefits

- Low V_{CEsat} (BISS) transistor and resistor-equipped transistor in one package
- Low threshold voltage (< 1 V) compared to MOSFET
- · Low drive power required
- Space-saving solution
- · Reduction of component count
- AEC-Q101 qualified

3. Applications

- · Supply line switches
- · Battery charger switches
- · High-side switches for LEDs, drivers and backlights
- · Portable equipment

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
TR1; PNP low	V _{CEsat} transistor						
V _{CEO}	collector-emitter voltage	open base		-	-	-60	V
I _C	collector current		[1]	-	-	-1	Α
R _{CEsat}	collector-emitter saturation resistance	I_C = -1000 mA; I_B = -100 mA; T_{amb} = 25 °C	[2]	-	255	340	mΩ
TR2; NPN resis	stor-equipped transistor	7		•			
V _{CEO}	collector-emitter voltage	open base		-	-	50	V
Io	output current			-	-	100	mA
R1	bias resistor 1 (input)			3.3	4.7	6.1	kΩ
R2/R1	bias resistor ratio			0.8	1	1.2	

- [1] Device mounted on a ceramic PCB, Al₂O₃, standard footprint.
- [2] Pulse test: $t_p \le 300 \mu s$; $\delta \le 0.02$



60 V, 1 A PNP/NPN loadswitch double transistor

5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	E1	emitter TR1		C1 I2 GND2
2	B1	base TR1		
3	O2	output (collector) TR2	<u> </u>	R1 R2
4	GND2	GND (emitter) TR2		TR2
5	12	input (base) TR2	<u>∃</u> 1 <u>∃</u> 2 <u>∃</u> 3	TR1
6	C1	collector TR1	TSOP6 (SOT457)	E1 B1 O2
				sym036

6. Ordering information

Table 3. Ordering information

Type number	Package				
	Name	Description	Version		
PBLS6002D	TSOP6	plastic, surface-mounted package (SC-74; TSOP6); 6 leads	<u>SOT457</u>		

7. Marking

Table 4. Marking codes

Type number	Marking code
PBLS6002D	F2

8. Limiting values

Table 5. Limiting values

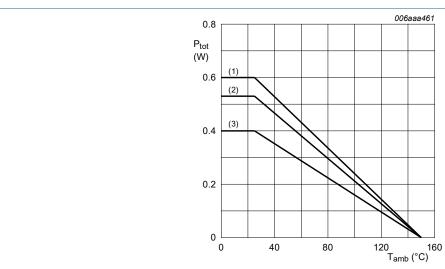
In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
TR1; PNP lov	w V _{CEsat} transistor					
V _{CBO}	collector-base voltage	open emitter		-	-80	V
V _{CEO}	collector-emitter voltage	open base		-	-60	V
V _{EBO}	emitter-base voltage	open collector		-	-5	V
I _C	collector current		[1]	-	-700	mA
			[2]	-	-850	mA
			[3]	-	-1	Α
I _{CM}	peak collector current	t _p ≤ 1 ms; single pulse		-	-2	Α
I _B	base current			-	-300	mA
I _{BM}	peak base current	single pulse; t _p ≤ 1 ms		-	-1000	mA
P _{tot}	total power dissipation	T _{amb} ≤ 25 °C	[1]	-	250	mW
			[2]	-	350	mW
			[3]	-	400	mW

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Symbol	Parameter	Conditions		Min	Max	Unit
TR2; NPN re	esistor-equipped transistor					
V _{CBO}	collector-base voltage	open emitter		-	50	V
V _{CEO}	collector-emitter voltage	open base		-	50	V
V _{EBO}	emitter-base voltage	open collector		-	10	V
V _I	input voltage			-10	30	V
Io	output current			-	100	mA
I _{CM}	peak collector current			-	100	mA
P _{tot}	total power dissipation		[1]	-	200	mW
			[2]	-	200	mW
			[3]	-	200	mW
Per device	<u>'</u>		'			
P _{tot}	total power dissipation	T _{amb} ≤ 25 °C	[1]	-	400	mW
			[2]	-	530	mW
			[3]	-	600	mW
T _j	junction temperature			-	150	°C
T _{amb}	ambient temperature			-65	150	°C
T _{stg}	storage temperature			-65	150	°C

- [1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.
- [2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 1 cm².
- [3] Device mounted on a ceramic PCB, Al₂O₃, standard footprint.



- (1) Ceramic PCB, Al₂O₃, standard footprint
- (2) FR4 PCB, mounting pad for collector 1 cm²
- (3) FR4 PCB, standard footprint

Fig. 1. Power derating curves

60 V, 1 A PNP/NPN loadswitch double transistor

9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
Per device							
R _{th(j-a)}	thermal resistance from	in free air	[1]	-	-	312	K/W
	junction to ambient		[2]	-	-	236	K/W
			[3]	-	-	208	K/W
TR1; PNP lo	w V _{CEsat} transistor		1				_
$R_{th(j-sp)}$	thermal resistance from junction to solder point			-	-	105	K/W

- [1] Device mounted on an FR4 PCB, single-sided, copper, tin-plated and standard footprint.
- [2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 1 cm².
- [3] Device mounted on a ceramic PCB, Al₂O₃, standard footprint.

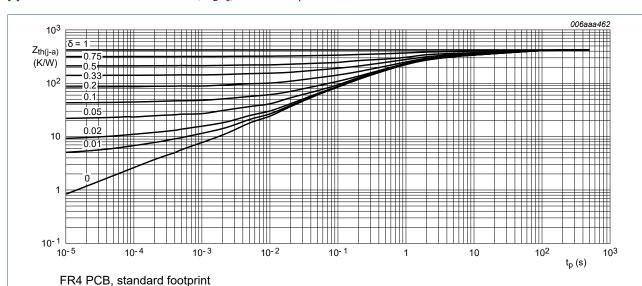


Fig. 2. TR1 (PNP): Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

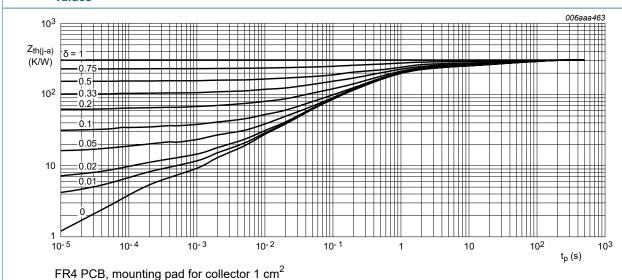
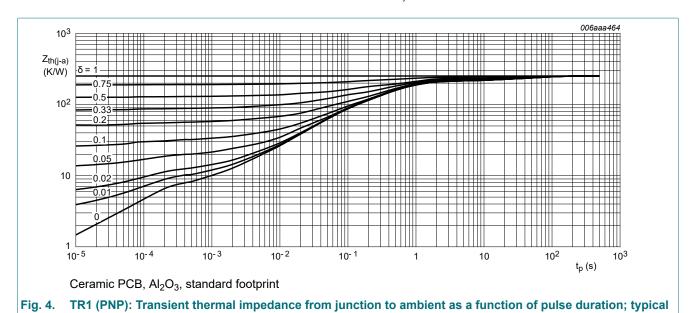


Fig. 3. TR1 (PNP): Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

PBLS6002D

60 V, 1 A PNP/NPN loadswitch double transistor



10. Characteristics

Table 7. Characteristics

values

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
TR1; PNP Id	ow V _{CEsat} transistor						
I _{CBO}	collector-base cut-off	V _{CB} = -60 V; I _E = 0 A; T _{amb} = 25 °C		-	-	-100	nA
	current	V _{CB} = -60 V; I _E = 0 A; T _j = 150 °C		-	-	-50	μΑ
I _{CES}	collector-emitter cut-off current	$V_{CE} = -60 \text{ V}; V_{BE} = 0 \text{ V}; T_{amb} = 25 \text{ °C}$		-	-	-100	nA
I _{EBO}	emitter-base cut-off current	$V_{EB} = -5 \text{ V}; I_{C} = 0 \text{ A}; T_{amb} = 25 \text{ °C}$		-	-	-100	nA
h _{FE}	DC current gain	V_{CE} = -5 V; I_{C} = -1 mA; T_{amb} = 25 °C		200	350	-	
		V_{CE} = -5 V; I_{C} = -500 mA; T_{amb} = 25 °C	[1]	150	230	-	
		V_{CE} = -5 V; I_{C} = -1000 mA; T_{amb} = 25 °C	[1]	100	160	-	
V _{CEsat}	collector-emitter	I_C = -100 mA; I_B = -1 mA; T_{amb} = 25 °C		-	-110	-175	mV
	saturation voltage	I_C = -500 mA; I_B = -50 mA; T_{amb} = 25 °C	[1]	-	-135	-180	mV
		I _C = -1000 mA; I _B = -100 mA;	[1]	-	-255	-340	mV
R _{CEsat}	collector-emitter saturation resistance	T _{amb} = 25 °C	[1]	-	255	340	mΩ
V _{BEsat}	base-emitter saturation voltage	I_C = -1000 mA; I_B = -50 mA; T_{amb} = 25 °C	[1]	-	-0.95	-1.1	V
V_{BEon}	base-emitter turn-on voltage	$V_{CE} = -5 \text{ V}; I_{C} = -1000 \text{ mA}; T_{amb} = 25 ^{\circ}\text{C}$	[1]	-	-0.82	-0.9	V
t _d	delay time	$I_C = -0.5 \text{ A}$; $I_{Bon} = -25 \text{ mA}$; $I_{Boff} = 25 \text{ mA}$;		-	11	-	ns
t _r	rise time	T _{amb} = 25 °C		-	30	-	ns
t _{on}	turn-on time			-	41	-	ns
t _s	storage time			-	205	-	ns
t _f	fall time			-	55	-	ns
t _{off}	turn-off time	I_C = -0.5 A; I_{Bon} = 25 mA; I_{Boff} = 25 A; T_{amb} = 25 °C		-	260	-	ns

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Symbol	Parameter	Conditions		Min	Тур	Max	Unit
C _c	collector capacitance	$V_{CB} = -10 \text{ V}; I_E = 0 \text{ A}; i_e = 0 \text{ A};$ f = 1 MHz; $T_{amb} = 25 \text{ °C}$		-	9	15	pF
f _T	transition frequency	V_{CE} = -10 V; I_{C} = -50 mA; f = 100 MHz; T_{amb} = 25 °C		150	185	-	MHz
TR2; NPN re	esistor-equipped transisto	•					
I _{CBO}	collector-base cut-off current	V _{CB} = 50 V; I _E = 0 A; T _{amb} = 25 °C		-	-	100	nA
I _{CEO}	collector-emitter cut-off	V _{CE} = 30 V; I _B = 0 A; T _{amb} = 25 °C		-	-	1	μΑ
	current	V _{CE} = 30 V; I _B = 0 A; T _j = 150 °C		-	-	50	μΑ
I _{EBO}	emitter-base cut-off current	$V_{EB} = 5 \text{ V}; I_{C} = 0 \text{ A}; T_{amb} = 25 ^{\circ}\text{C}$		-	-	900	μΑ
h _{FE}	DC current gain	V _{CE} = 5 V; I _C = 20 mA; T _{amb} = 25 °C		30	-	-	
V _{CEsat}	collector-emitter saturation voltage	$I_C = 10 \text{ mA}; I_B = 0.5 \text{ mA}; T_{amb} = 25 ^{\circ}\text{C}$	[1]	-	-	150	mV
$V_{I(off)}$	off-state input voltage	V _{CE} = 5 V; I _C = 100 μA; T _{amb} = 25 °C		-	1.1	0.5	V
V _{I(on)}	on-state input voltage	V _{CE} = 0.3 V; I _C = 20 mA; T _{amb} = 25 °C		2.5	1.9	-	V
R1	bias resistor 1 (input)			3.3	4.7	6.1	kΩ
R2/R1	bias resistor ratio			0.8	1	1.2	
C _c	collector capacitance	V_{CB} = 10 V; I_{E} = 0 A; i_{e} = 0 A; f = 1 MHz; T_{amb} = 25 °C		-	-	2.5	pF

[1] Pulse test: $t_p \le 300 \mu s$; $\delta \le 0.02$

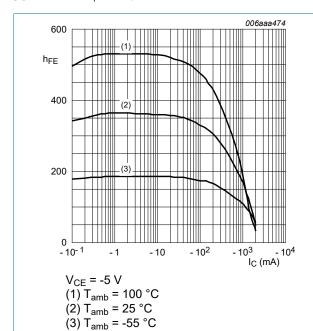
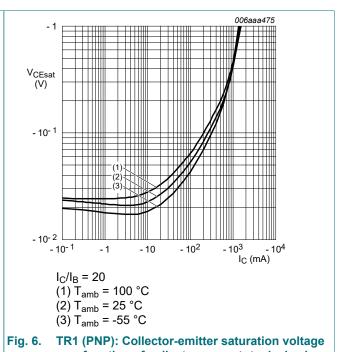


Fig. 5. TR1 (PNP): DC current gain as a function of collector current; typical values



as a function of collector current; typical values

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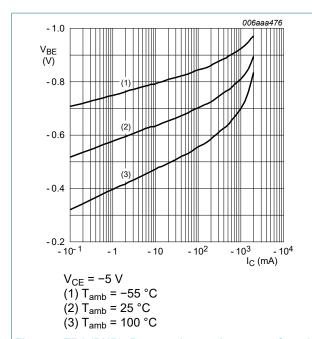


Fig. 7. TR1 (PNP): Base-emitter voltage as a function of collector current; typical values

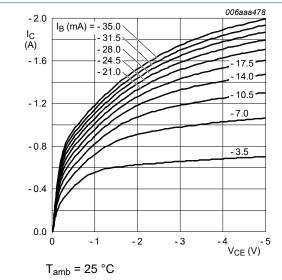
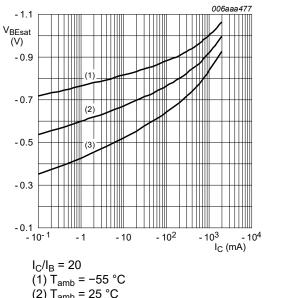
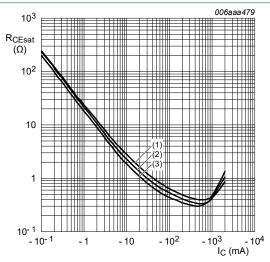


Fig. 9. TR1 (PNP): Collector current as a function of collector-emitter voltage; typical values



 $(1) T_{amb} = -55 °C$ (2) $T_{amb} = 25 °C$ (3) $T_{amb} = 100 \, ^{\circ}C$

Fig. 8. TR1 (PNP): Base-emitter saturation voltage as a function of collector current; typical values



 $I_{\rm C}/I_{\rm B} = 20$ (1) T_{amb} = 100 °C (2) $T_{amb} = 25 \, ^{\circ}C$ (3) $T_{amb} = -55 \, ^{\circ}C$

Fig. 10. TR1 (PNP): Collector-emitter saturation resistance as a function of collector current; typical values

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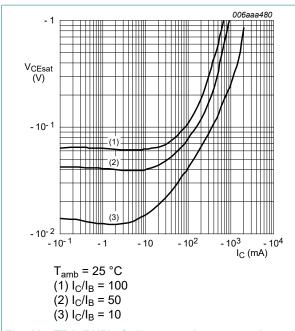
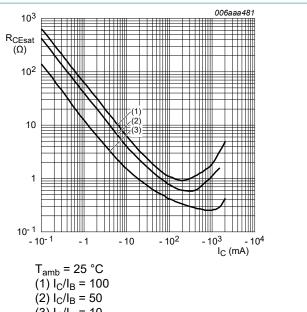


Fig. 11. TR1 (PNP): Collector-emitter saturation voltage as a function of collector current; typical values



(2) $I_C/I_B = 50$ (3) $I_C/I_B = 10$

Fig. 12. TR1 (PNP): Collector-emitter saturation resistance as a function of collector current; typical values

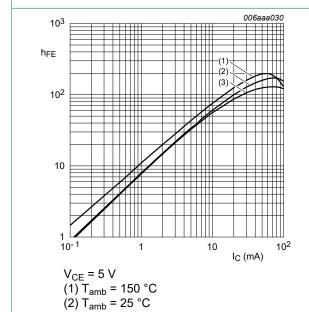
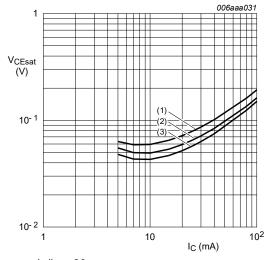


Fig. 13. TR2 (NPN): DC current gain as a function of collector current; typical values

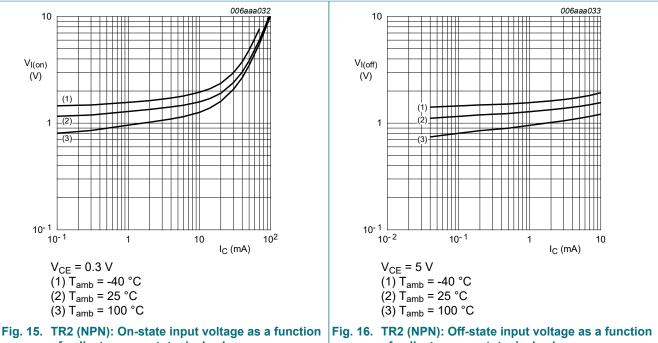
(3) $T_{amb} = -40 \, ^{\circ}C$



 $I_C/I_B = 20$ (1) T_{amb} = 100 °C (2) $T_{amb} = 25 \, ^{\circ}C$ (3) $T_{amb} = -40 \, ^{\circ}C$

Fig. 14. TR2 (NPN): Collector-emitter saturation voltage as a function of collector current; typical values

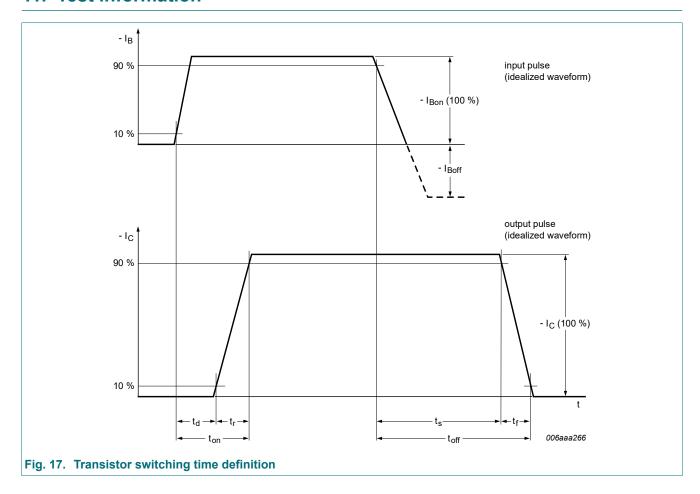
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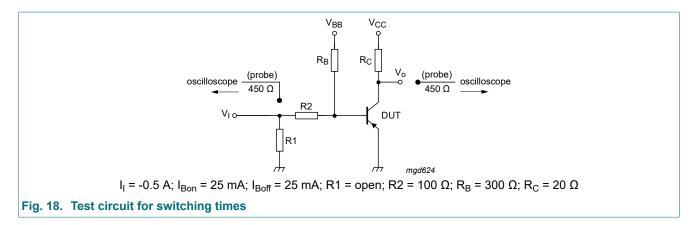
of collector current; typical values

of collector current; typical values

11. Test information



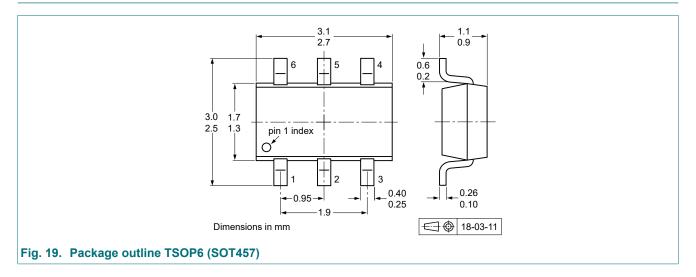
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Quality information

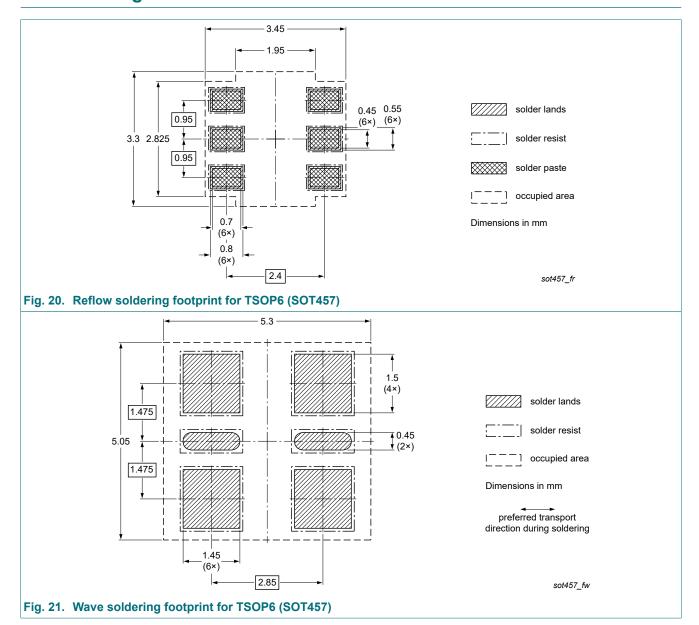
This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard *Q101 - Stress test qualification for discrete semiconductors*, and is suitable for use in automotive applications.

12. Package outline



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13. Soldering



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14. Revision history

Table 8. Revision history

Data sheet ID	Release date	Data sheet status	Change notice	Supersedes		
PBLS6002D v.3	20231026	Product data sheet	-	PBLS6002D_2		
Modifications:	 The format of this data sheet has been redesigned to comply with the identity guidelines of Nexperia. Legal texts have been adapted to the new company name where appropriate. Section "Packing information" removed. 					
PBLS6002D_2	20090907	Product data sheet	-	PBLS6002D_1		
PBLS6002D_1	20050623	Product data sheet	-	-		

15. Legal information

Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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